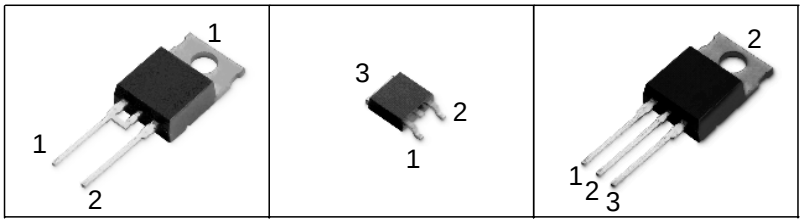
Silicon Carbide Schottky Diode

- Worlds first 600V Schottky diode
- Revolutionary semiconductor material - Silicon Carbide
- Switching behavior benchmark
- No reverse recovery
- No temperature influence on the switching behavior
- Ideal diode for Power Factor Correction up to 800W[F)]
- No forward recovery

Product Summary

V_{RRM}	600	V
Q_c	13	nC
I_F	4	A

P-TO220-2-2. P-TO252-3-1. P-TO220-3-1.



Type	Package	Ordering Code	Marking	Pin 1	PIN 2	PIN 3
SDP04S60	P-TO220-3-1.	Q67040-S4369	D04S60	n.c.	C	A
SDD04S60	P-TO252-3-1.	Q67040-S4368	D04S60	n.c.	A	C
SDT04S60	P-TO220-2-2.	Q67040-S4445	D04S60	C	A	

Maximum Ratings,at T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Value	Unit
Continuous forward current, T_C=100°C	I_F	4	A
RMS forward current, f=50Hz	I_{FRMS}	5.6	
Surge non repetitive forward current, sine halfwave T_C=25°C, t_p=10ms	I_{FSM}	12.5	
Repetitive peak forward current T_j=150°C, T_C=100°C, D=0.1	I_{FRM}	18	
Non repetitive peak forward current t_p=10µs, T_C=25°C	I_{FMAX}	40	
i^2t value, T_C=25°C, t_p=10ms	$\int i^2 dt$	0.78	A²s
Repetitive peak reverse voltage	V_{RRM}	600	V
Surge peak reverse voltage	V_{RSM}	600	
Power dissipation, T_C=25°C	P_{tot}	36.5	W
Operating and storage temperature	T_j , T_{stg}	-55... +175	°C

Thermal Characteristics

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Characteristics					
Thermal resistance, junction - case	R_{thJC}	-	-	4.1	K/W
Thermal resistance, junction - ambient, leaded	R_{thJA}	-	-	62	
SMD version, device on PCB:	R_{thJA}				
P-TO263-3-2: @ min. footprint		-	-	62	
P-TO263-3-2: @ 6 cm^2 cooling area [2)]		-	35	-	
P-TO252-3-1: @ min. footprint		-	-	75	
P-TO252-3-1: @ 6 cm^2 cooling area [2)]		-	-	50	

Electrical Characteristics, at T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Static Characteristics					
Diode forward voltage	V_F				V
I_F=4A, T_j=25°C		-	1.7	1.9	
I_F=4A, T_j=150°C		-	2	2.4	
Reverse current	I_R				µA
V_R=600V, T_j=25°C		-	15	200	
V_R=600V, T_j=150°C		-	40	1000	

[1]CCM, V_{IN}= 85VAC, T_j = 150°C, T_C =100°C, η = 93%, ΔI_{IN} = 30%

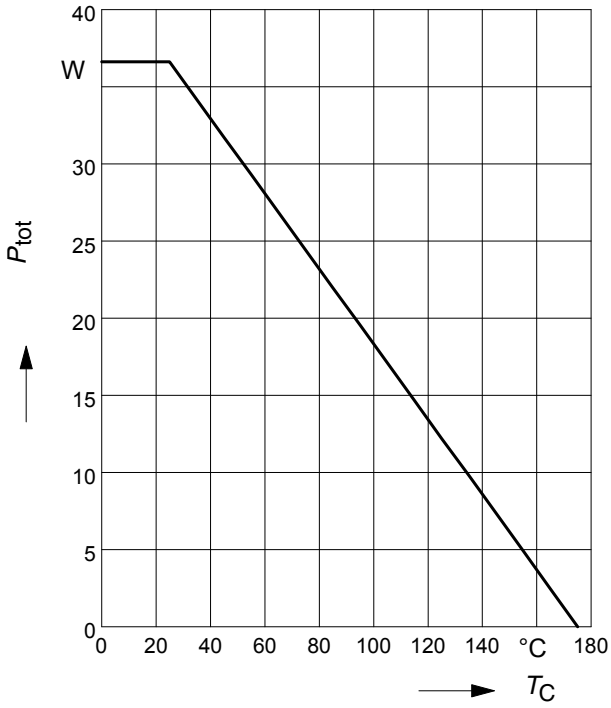
[2]Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70 µm thick) copper area for drain connection. PCB is vertical without blown air.

Electrical Characteristics, at T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics					
Total capacitive charge V_R=400V, I_F=4A, di_F/dt=200A/µs, T_j=150°C	Q_c	-	13	-	nC
Switching time V_R=400V, I_F=4A, di_F/dt=200A/µs, T_j=150°C	t_{rr}	-	n.a.	-	ns
Total capacitance	C				pF
V_R=0V, T_C=25°C, f=1MHz		-	150	-	
V_R=300V, T_C=25°C, f=1MHz		-	10	-	
V_R=600V, T_C=25°C, f=1MHz		-	7	-	

1 Power dissipation

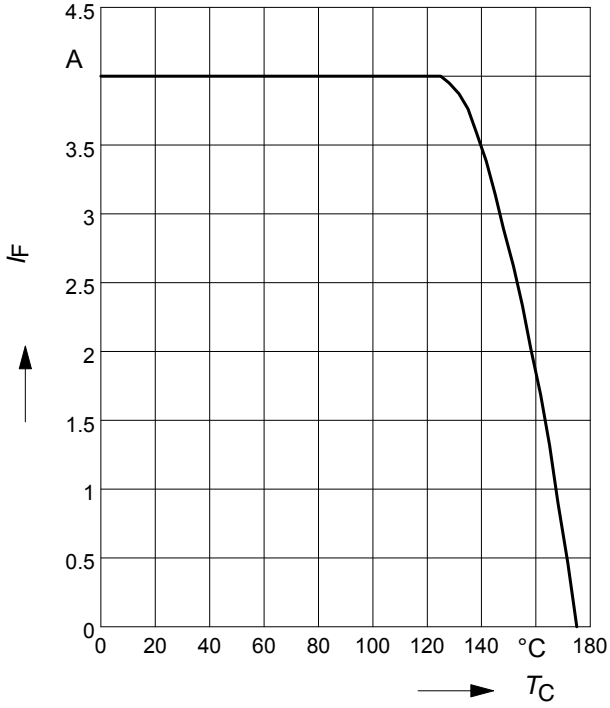
$P_{tot} = f(T_C)$



2 Diode forward current

$I_F = f(T_C)$

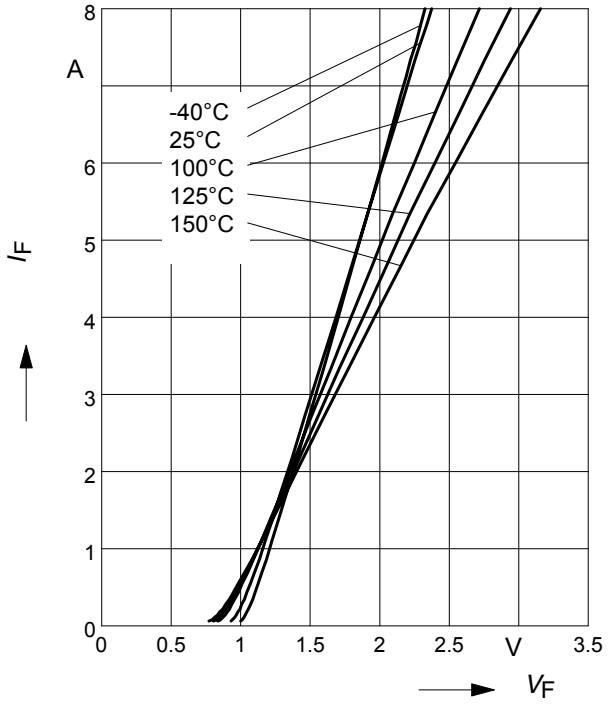
parameter: $T_j \leq 175$ °C



3 Typ. forward characteristic

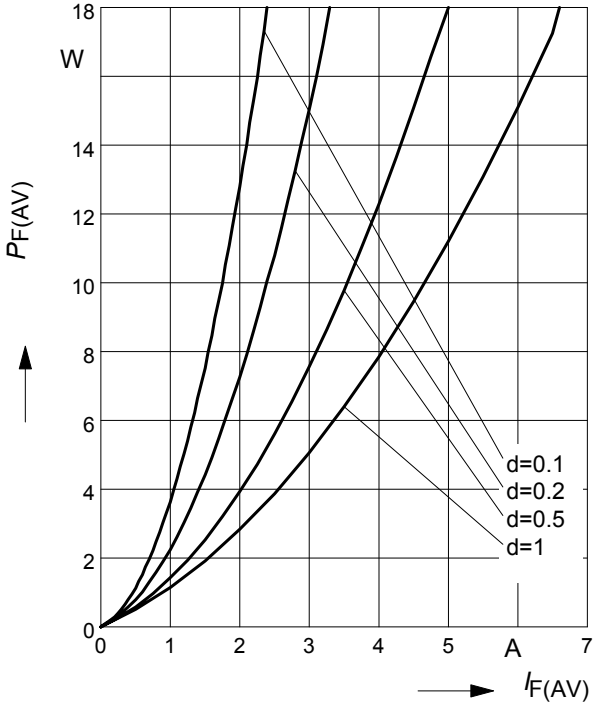
$I_F = f(V_F)$

parameter: T_j , tp = 350 µs



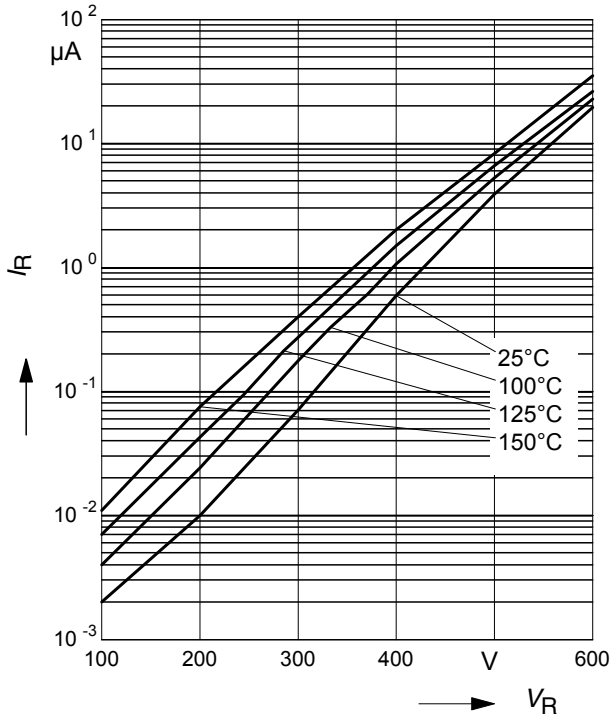
4 Typ. forward power dissipation vs. average forward current

$P_{F(AV)}=f(I_F)$ T_C=100°C, $d = t_p/T$



5 Typ. reverse current vs. reverse voltage

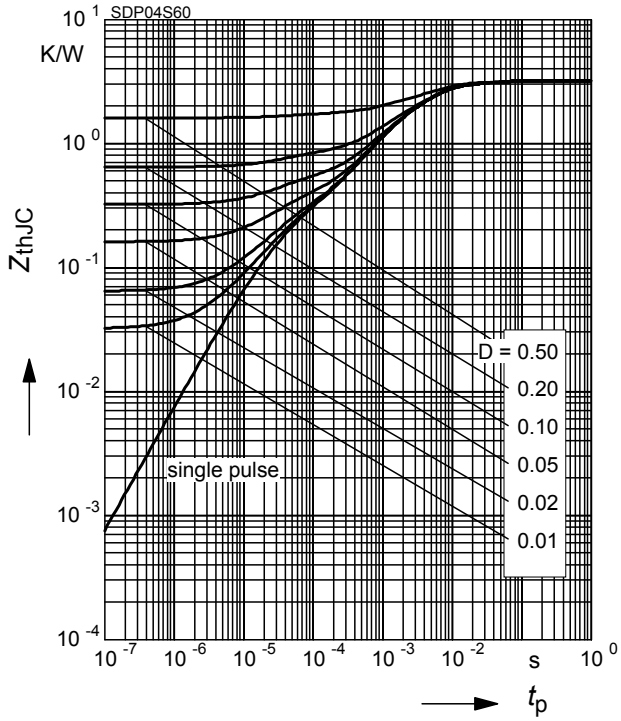
$I_R = f(V_R)$



6 Transient thermal impedance

$Z_{thJC} = f(t_p)$

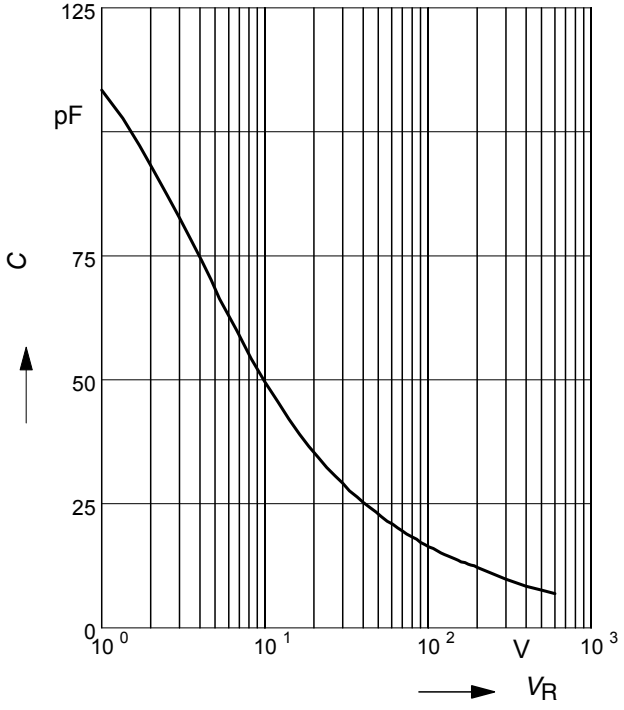
parameter : $D = t_p/T$



7 Typ. capacitance vs. reverse voltage

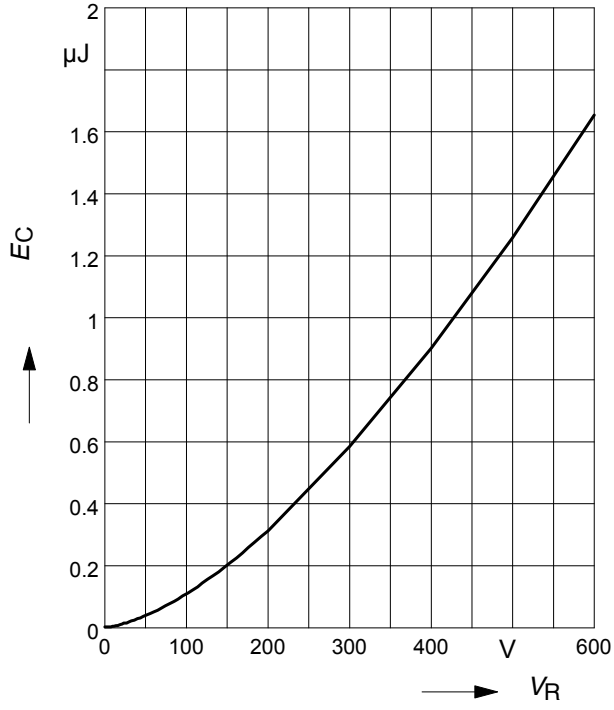
$C = f(V_R)$

parameter: T_C = 25 °C, f = 1 MHz



8 Typ. C stored energy

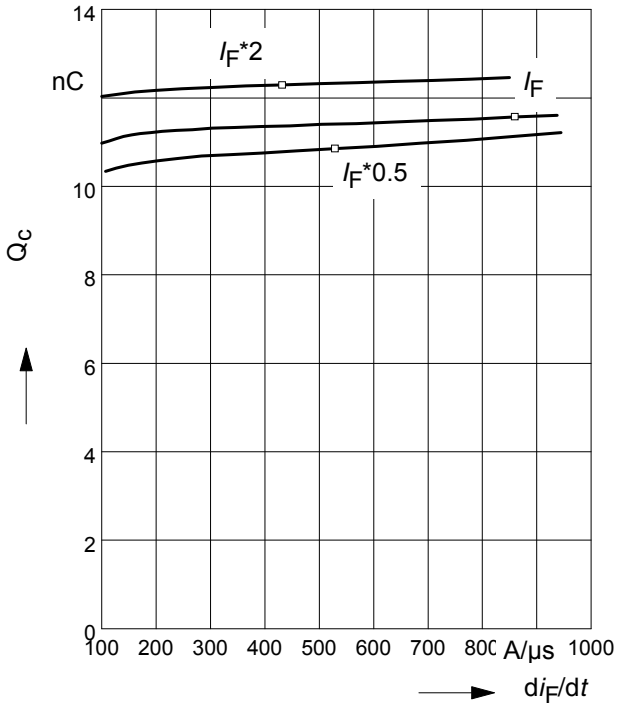
$E_C = f(V_R)$



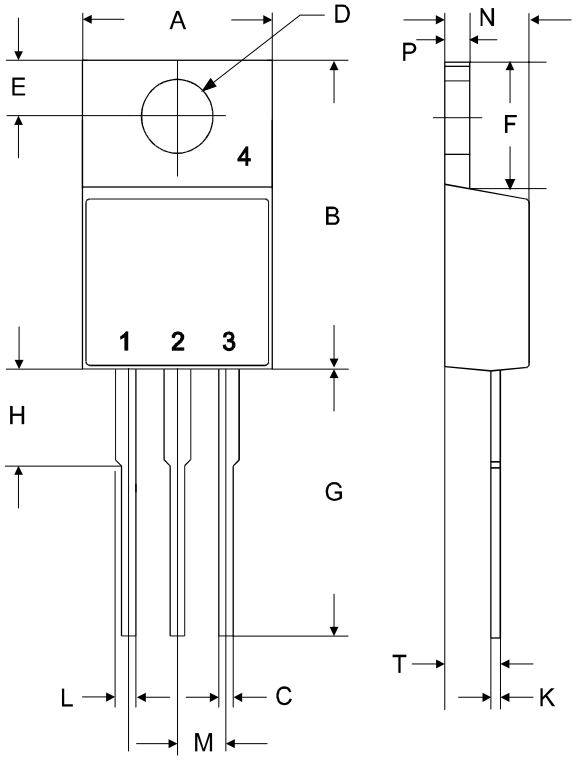
9 Typ. capacitive charge vs. current slope

$Q_c = f(di_F/dt)$

parameter: T_j = 150 °C

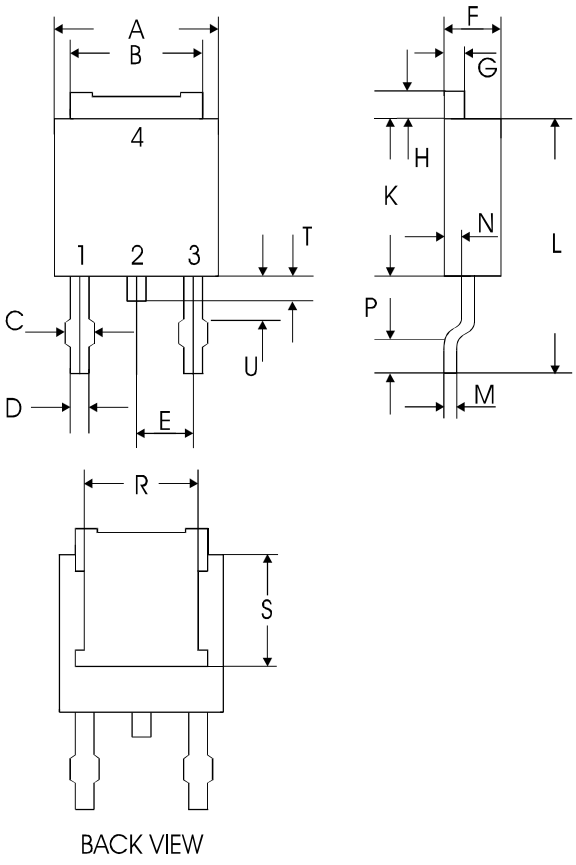


P-TO220-3-1

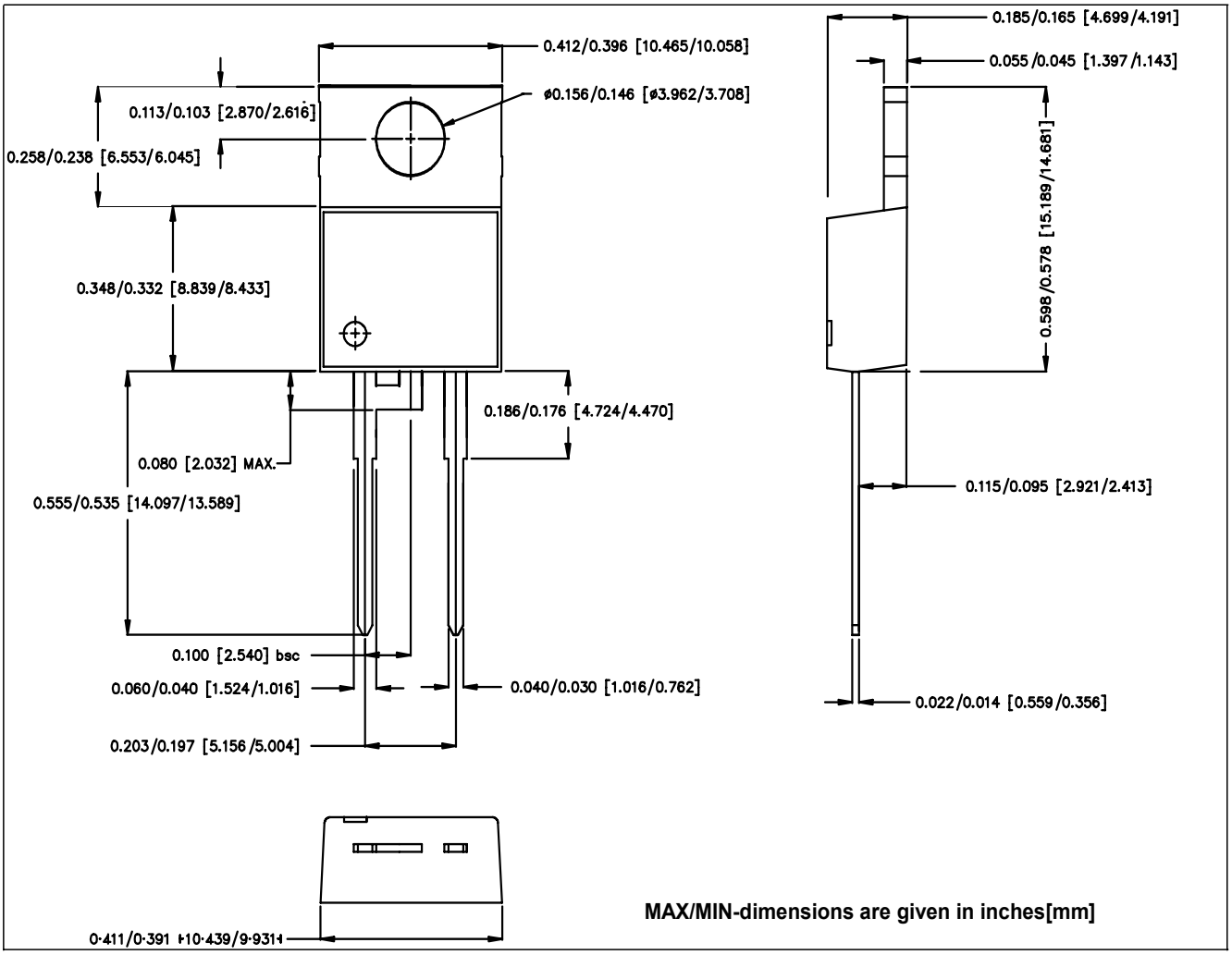


symbol	dimensions			
	[mm]		[inch]	
	min	max	min	max
A	9.70	10.30	0.3819	0.4055
B	14.88	15.95	0.5858	0.6280
C	0.65	0.86	0.0256	0.0339
D	3.55	3.89	0.1398	0.1531
E	2.60	3.00	0.1024	0.1181
F	6.00	6.80	0.2362	0.2677
G	13.00	14.00	0.5118	0.5512
H	4.35	4.75	0.1713	0.1870
K	0.38	0.65	0.0150	0.0256
L	0.95	1.32	0.0374	0.0520
M	2.54 typ.		0.1 typ.	
N	4.30	4.50	0.1693	0.1772
P	1.17	1.40	0.0461	0.0551
T	2.30	2.72	0.0906	0.1071

P-TO252 (D-Pak)



symbol	dimensions			
	[mm]		inch]	
	min	max	min	max
A	6.40	6.73	0.2520	0.2650
B	5.25	5.50	0.2067	0.2165
C	(0.65)	(1.15)	(0.0256)	(0.0453)
D	0.63	0.89	0.0248	0.0350
E	2.28		0.2520	
F	2.19	2.39	0.0862	0.0941
G	0.76	0.98	0.0299	0.0386
H	0.90	1.21	0.0354	0.0476
K	5.97	6.23	0.2350	0.2453
L	9.40	10.40	0.3701	0.4094
M	0.46	0.58	0.0181	0.0228
N	0.87	1.15	0.0343	0.0453
P	0.51	-	0.0201	-
R	5.00	-	0.1969	-
S	4.17	-	0.1642	-
T	0.26	1.02	0.0102	0.0402
U	-	-	-	-


0.412/0.396 [10.465/10.058]
ø0.156/0.146 [ø3.962/3.708]
0.113/0.103 [2.870/2.616]
0.258/0.238 [6.553/6.045]
0.348/0.332 [8.839/8.433]
0.186/0.176 [4.724/4.470]
0.080 [2.032] MAX.
0.555/0.535 [14.097/13.589]
0.100 [2.540] bsc
0.060/0.040 [1.524/1.016]
0.040/0.030 [1.016/0.762]
0.203/0.197 [5.156/5.004]
0.411/0.391 [10.439/9.931]
0.185/0.165 [4.699/4.191]
0.055/0.045 [1.397/1.143]
0.598/0.578 [15.189/14.681]
0.115/0.095 [2.921/2.413]
0.022/0.014 [0.559/0.356]
MAX/MIN-dimensions are given in inches[mm]

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